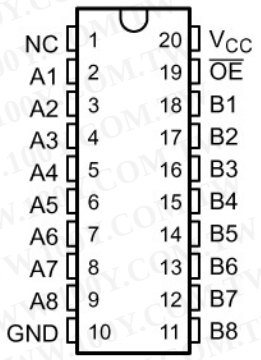
FEATURES

- High-Bandwidth Data Path (up to 500 MHz (1))
- Equivalent to IDTQS3VH384 Device
- 5-V Tolerant I/Os With Device Powered Up or Powered Down
- Low and Flat ON-State Resistance (r_{on}) Characteristics Over Operating Range (r_{on} = 4 Ω Typ)
- Rail-to-Rail Switching on Data I/O Ports
  - 0- to 5-V Switching With 3.3-V V_{CC}
  - 0- to 3.3-V Switching With 2.5-V V_{CC}
- Bidirectional Data Flow With Near-Zero Propagation Delay
- Low Input/Output Capacitance Minimizes Loading and Signal Distortion ($C_{io(OFF)}$ = 3.5 pF Typ)
- Fast Switching Frequency (f_{OE} = 20 MHz Max)
- Data and Control Inputs Provide Undershoot Clamp Diodes
- Low Power Consumption (I_{CC} = 1 mA Typical)
- V_{CC} Operating Range From 2.3 V to 3.6 V
- Data I/Os Support 0- to 5-V Signaling Levels (0.8 V, 1.2 V, 1.5 V, 1.8 V, 2.5 V, 3.3 V, 5 V)
- Control Inputs Can Be Driven by TTL or 5-V/3.3-V CMOS Outputs
- I_{off} Supports Partial-Power-Down Mode Operation
- Latch-Up Performance Exceeds 100 mA Per JESD 78, Class II
- ESD Performance Tested Per JESD 22
  - 2000-V Human-Body Model (A114-B, Class II)
  - 1000-V Charged-Device Model (C101)
- Supports Both Digital and Analog Applications: PCI Interface, Differential Signal Interface, Memory Interleaving, Bus Isolation, Low-Distortion Signal Gating

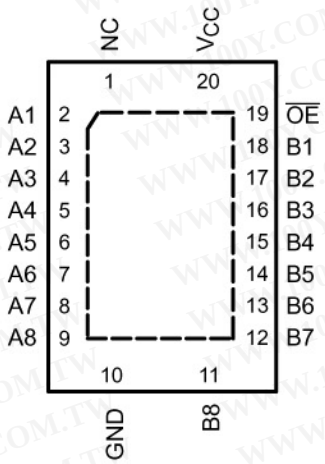
(1) For additional information regarding the performance characteristics of the CB3Q family, refer to the TI application report, *CBT-C, CB3T, and CB3Q Signal-Switch Families*, literature number SCDA008.

DBQ, DGV, OR PW PACKAGE
(TOP VIEW)



NC - No internal connection

RGY PACKAGE
(TOP VIEW)



NC - No internal connection

DESCRIPTION/ORDERING INFORMATION

The SN74CB3Q3245 is a high-bandwidth FET bus switch utilizing a charge pump to elevate the gate voltage of the pass transistor, providing a low and flat ON-state resistance (r_{on}). The low and flat ON-state resistance allows for minimal propagation delay and supports rail-to-rail switching on the data input/output (I/O) ports. The device also features low data I/O capacitance to minimize capacitive loading and signal distortion on the data bus. Specifically designed to support high-bandwidth applications, the SN74CB3Q3245 provides an optimized interface solution ideally suited for broadband communications, networking, and data-intensive computing systems.

DESCRIPTION/ORDERING INFORMATION (CONTINUED)

The SN74CB3Q3245 is organized as an 8-bit bus switch with a single output-enable ($\overline{OE}$) input. When $\overline{OE}$ is low, the bus switch is ON and the A port is connected to the B port, allowing bidirectional data flow between ports. When $\overline{OE}$ is high, the bus switch is OFF and a high-impedance state exists between the A and B ports.

This device is fully specified for partial-power-down applications using I_{off}. The I_{off} circuitry prevents damaging current backflow through the device when it is powered down. The device has isolation during power off.

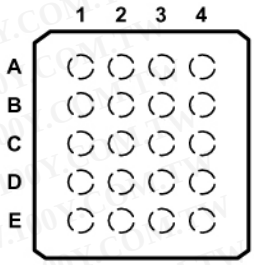
To ensure the high-impedance state during power up or power down, $\overline{OE}$ should be tied to V_{CC} through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.

ORDERING INFORMATION

T_A	PACKAGE(1)		ORDERABLE PART NUMBER	TOP-SIDE MARKING
–40°C to 85°C	QFN – RGY	Tape and reel	SN74CB3Q3245RGYR	BU245
	SSOP (QSOP) – DBQ	Tape and reel	SN74CB3Q3245DBQR	CB3Q3245
	TSSOP – PW	Tube	SN74CB3Q3245PW	BU245
		Tape and reel	SN74CB3Q3245PWR	
	TVSOP – DGV	Tape and reel	SN74CB3Q3245DGVR	BU245
	VFBGA – GQN	Tape and reel	SN74CB3Q3245GQNR	BU245

(1) Package drawings, standard packing quantities, thermal data, symbolization, and PCB design guidelines are available at www.ti.com/sc/package.

GQN PACKAGE
(TOP VIEW)



TERMINAL ASSIGNMENTS(1)

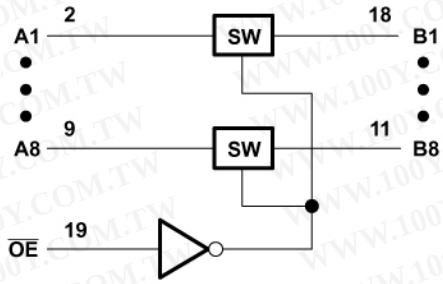
	1	2	3	4
A	A1	NC	V_{CC}	$\overline{OE}$
B	A3	B2	A2	B1
C	A5	A4	B4	B3
D	A7	B6	A6	B5
E	GND	A8	B8	B7

(1) NC - No internal connection

FUNCTION TABLE

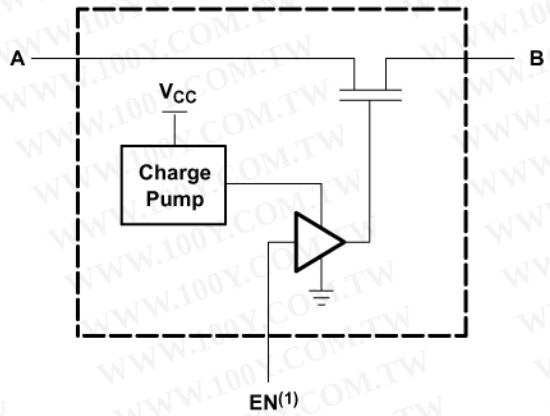
INPUT $\overline{OE}$	INPUT/OUTPUT A	FUNCTION
L	B	A port = B port
H	Z	Disconnect

LOGIC DIAGRAM (POSITIVE LOGIC)



Pin numbers shown are for the DBQ, DGV, PW, and RGY packages.

SIMPLIFIED SCHEMATIC, EACH FET SWITCH (SW)



(1) EN is the internal enable signal applied to the switch.

Absolute Maximum Ratings[1]

over operating free-air temperature range (unless otherwise noted)

			MIN	MAX	UNIT
V_{CC}	Supply voltage range		–0.5	4.6	V
V_{IN}	Control input voltage range[2][3]		–0.5	7	V
$V_{I/O}$	Switch I/O voltage range[2][3][4]		–0.5	7	V
I_{IK}	Control input clamp current	V_{IN} < 0		–50	mA
$I_{I/OK}$	I/O port clamp current	$V_{I/O}$ < 0		–50	mA
I_{IO}	ON-state switch current[5]			±64	mA
	Continuous current through V_{CC} or GND			±100	mA
θ_{JA}	Package thermal impedance	DBQ package[6]		68	°C/W
		DGV package[6]		92	
		GQN package[6]		78	
		PW package[6]		83	
		RGY package[7]		37	
T_{stg}	Storage temperature range		–65	150	°C

(1) Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.
(2) All voltages are with respect to ground, unless otherwise specified.
(3) The input and output voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
(4) V_I and V_O are used to denote specific conditions for $V_{I/O}$.
(5) I_I and I_O are used to denote specific conditions for $I_{I/O}$.
(6) The package thermal impedance is calculated in accordance with JESD 51-7.
(7) The package thermal impedance is calculated in accordance with JESD 51-5.

Recommended Operating Conditions[1]

			MIN	MAX	UNIT
V_{CC}	Supply voltage		2.3	3.6	V
V_{IH}	High-level control input voltage	V_{CC} = 2.3 V to 2.7 V	1.7	5.5	V
		V_{CC} = 2.7 V to 3.6 V	2	5.5	
V_{IL}	Low-level control input voltage	V_{CC} = 2.3 V to 2.7 V	0	0.7	V
		V_{CC} = 2.7 V to 3.6 V	0	0.8	
$V_{I/O}$	Data input/output voltage		0	5.5	V
T_A	Operating free-air temperature		–40	85	°C

(1) All unused control inputs of the device must be held at V_{CC} or GND to ensure proper device operation. Refer to the TI application report, *Implications of Slow or Floating CMOS Inputs*, literature number SCBA004.

Electrical Characteristics(1)

over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER		TEST CONDITIONS			MIN	TYP(2)	MAX	UNIT
V_{IK}		V_{CC} = 3.6 V,	I_I = –18 mA				–1.8	V
I_{IN}	Control inputs	V_{CC} = 3.6 V,	V_{IN} = 0 to 5.5 V				±1	µA
I_{OZ}(3)		V_{CC} = 3.6 V,	V_O = 0 to 5.5 V, V_I = 0,	Switch OFF, V_{IN} = V_{CC} or GND			±1	µA
I_{off}		V_{CC} = 0,	V_O = 0 to 5.5 V,	V_I = 0			1	µA
I_{CC}		V_{CC} = 3.6 V,	$I_{I/O}$ = 0, Switch ON or OFF,	V_{IN} = V_{CC} or GND		1	2	mA
ΔI_{CC}(4)	Control inputs	V_{CC} = 3.6 V,	One input at 3 V,	Other inputs at V_{CC} or GND			30	µA
I_{CCD}(5)	Per control input	V_{CC} = 3.6 V, Control input switching at 50% duty cycle	A and B ports open,			0.30	0.35	mA/ MHz
C_{in}	Control inputs	V_{CC} = 3.3 V,	V_{IN} = 5.5 V, 3.3 V, or 0			2.5	3.5	pF
$C_{io(OFF)}$		V_{CC} = 3.3 V,	Switch OFF, V_{IN} = V_{CC} or GND,	$V_{I/O}$ = 5.5 V, 3.3 V, or 0		3.5	5	pF
$C_{io(ON)}$		V_{CC} = 3.3 V,	Switch ON, V_{IN} = V_{CC} or GND,	$V_{I/O}$ = 5.5 V, 3.3 V, or 0		9	11	pF
r_{on}(6)		V_{CC} = 2.3 V, TYP at V_{CC} = 2.5 V	V_I = 0,	I_O = 30 mA		4	8	Ω
			V_I = 1.7 V,	I_O = –15 mA		4.5	9	
		V_{CC} = 3 V	V_I = 0,	I_O = 30 mA		4	6	
			V_I = 2.4 V,	I_O = –15 mA		4	8	

(1) V_{IN} and I_{IN} refer to control inputs. V_I, V_O, I_I, and I_O refer to data pins.
(2) All typical values are at V_{CC} = 3.3 V (unless otherwise noted), T_A = 25°C.
(3) For I/O ports, the parameter I_{OZ} includes the input leakage current.
(4) This is the increase in supply current for each input that is at the specified TTL voltage level, rather than V_{CC} or GND.
(5) This parameter specifies the dynamic power-supply current associated with the operating frequency of a single control input (see Figure 2).
(6) Measured by the voltage drop between the A and B terminals at the indicated current through the switch. ON-state resistance is determined by the lower of the voltages of the two (A or B) terminals.

Switching Characteristics

over recommended operating free-air temperature range (unless otherwise noted) (see Figure 3)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	V_{CC} = 2.5 V ± 0.2 V		V_{CC} = 3.3 V ± 0.3 V		UNIT
			MIN	MAX	MIN	MAX	
$f_{\overline{OE}}$(1)	$\overline{OE}$	A or B		10		20	MHz
t_{pd}(2)	A or B	B or A		0.12		0.20	ns
t_{en}	$\overline{OE}$	A or B	1.5	7.5	1.5	6.5	ns
t_{dis}	$\overline{OE}$	A or B	1	6.5	1	6.5	ns

(1) Maximum switching frequency for control input (V_O > V_{CC}, V_I = 5 V, R_L ≥ 1 MΩ, C_L = 0)
(2) The propagation delay is the calculated RC time constant of the typical ON-state resistance of the switch and the specified load capacitance, when driven by an ideal voltage source (zero output impedance).

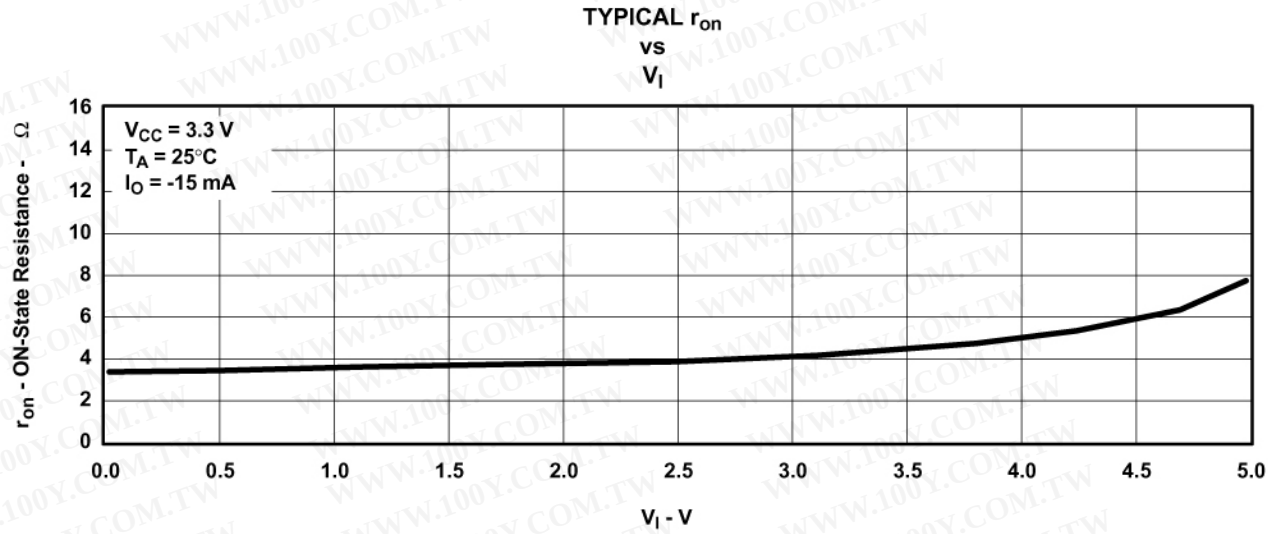


Figure 1. Typical r_{on} vs V_I

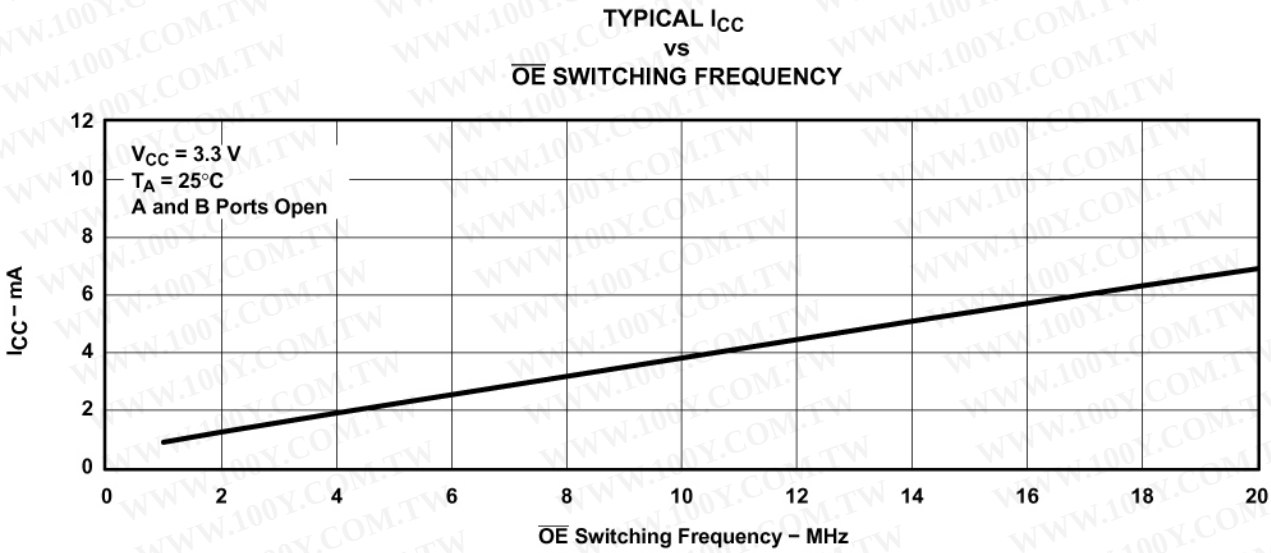
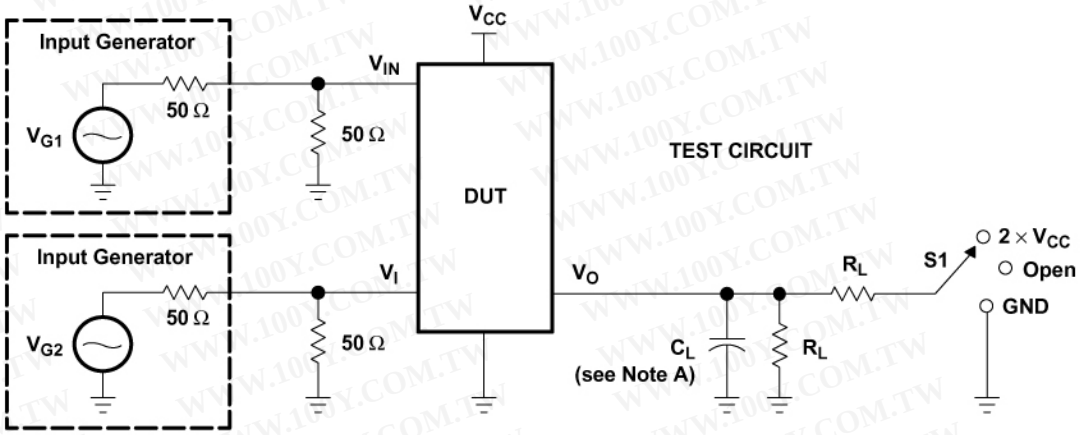
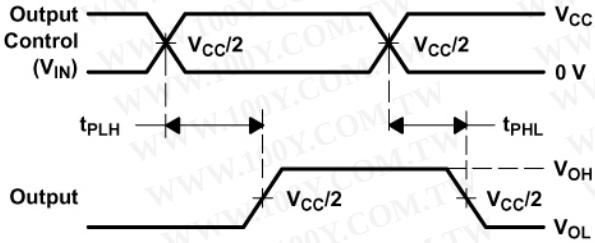


Figure 2. Typical I_{CC} vs $\overline{OE}$ Switching Frequency

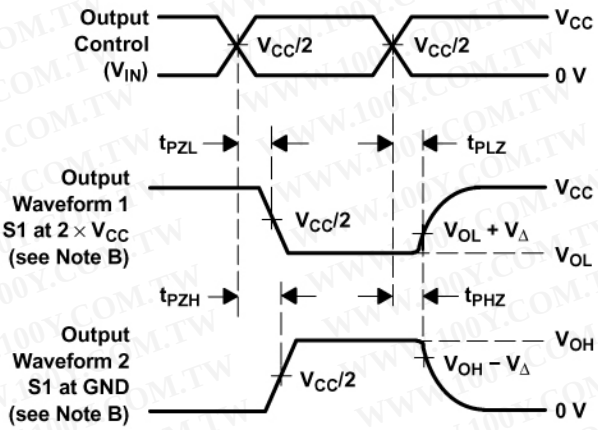
PARAMETER MEASUREMENT INFORMATION



TEST	V_{CC}	S1	R_L	V_I	C_L	V_Δ
$t_{pd(s)}$	2.5 V ± 0.2 V 3.3 V ± 0.3 V	Open Open	500 Ω 500 Ω	V_{CC} or GND V_{CC} or GND	30 pF 50 pF	
t_{PLZ}/t_{PZL}	2.5 V ± 0.2 V 3.3 V ± 0.3 V	2 × V_{CC} 2 × V_{CC}	500 Ω 500 Ω	GND GND	30 pF 50 pF	0.15 V 0.3 V
t_{PHZ}/t_{PZH}	2.5 V ± 0.2 V 3.3 V ± 0.3 V	GND GND	500 Ω 500 Ω	V_{CC} V_{CC}	30 pF 50 pF	0.15 V 0.3 V



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES ($t_{pd(s)}$)



VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low, except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high, except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.
D. The outputs are measured one at a time, with one transition per measurement.
E. t_{PLZ} and t_{PHZ} are the same as t_{dis}.
F. t_{PZL} and t_{PZH} are the same as t_{en}.
G. t_{PLH} and t_{PHL} are the same as $t_{pd(s)}$. The tpd propagation delay is the calculated RC time constant of the typical ON-state resistance of the switch and the specified load capacitance, when driven by an ideal voltage source (zero output impedance).
H. All parameters and waveforms are not applicable to all devices.

Figure 3. Test Circuit and Voltage Waveforms

PACKAGING INFORMATION

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead/Ball Finish	MSL Peak Temp (3)
74CB3Q3245DBQRE4	ACTIVE	SSOP/ QSOP	DBQ	20	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR
74CB3Q3245DBQRG4	ACTIVE	SSOP/ QSOP	DBQ	20	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR
74CB3Q3245DGVRE4	ACTIVE	TVSOP	DGV	20	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
74CB3Q3245DGVRG4	ACTIVE	TVSOP	DGV	20	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
74CB3Q3245RGYRG4	ACTIVE	VQFN	RGY	20	1000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR
SN74CB3Q3245DBQR	ACTIVE	SSOP/ QSOP	DBQ	20	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR
SN74CB3Q3245DGVR	ACTIVE	TVSOP	DGV	20	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
SN74CB3Q3245GQNR	NRND	BGA MI CROSTA R JUNI OR	GQN	20	1000	TBD	SNPB	Level-1-240C-UNLIM
SN74CB3Q3245PW	ACTIVE	TSSOP	PW	20	70	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
SN74CB3Q3245PWE4	ACTIVE	TSSOP	PW	20	70	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
SN74CB3Q3245PWG4	ACTIVE	TSSOP	PW	20	70	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
SN74CB3Q3245PWR	ACTIVE	TSSOP	PW	20	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
SN74CB3Q3245PWRE4	ACTIVE	TSSOP	PW	20	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
SN74CB3Q3245PWRG4	ACTIVE	TSSOP	PW	20	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
SN74CB3Q3245RGYR	ACTIVE	VQFN	RGY	20	1000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR
SN74CB3Q3245ZQNR	ACTIVE	BGA MI CROSTA R JUNI OR	ZQN	20	1000	Green (RoHS & no Sb/Br)	SNAGCU	Level-1-260C-UNLIM

(1) The marketing status values are defined as follows:
ACTIVE: Product device recommended for new designs.
LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.
NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.
PREVIEW: Device has been announced but is not in production. Samples may or may not be available.
OBSOLETE: TI has discontinued the production of the device.

(2) Eco Plan - The planned eco-friendly classification: Pb-Free (RoHS), Pb-Free (RoHS Exempt), or Green (RoHS & no Sb/Br) - please check for the latest availability information and additional product content details.
TBD: The Pb-Free/Green conversion plan has not been defined.
Pb-Free (RoHS): TI's terms "Lead-Free" or "Pb-Free" mean semiconductor products that are compatible with the current RoHS requirements for all 6 substances, including the requirement that lead not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, TI Pb-Free products are suitable for use in specified lead-free processes.
Pb-Free (RoHS Exempt): This component has a RoHS exemption for either 1) lead-based flip-chip solder bumps used between the die and package, or 2) lead-based die adhesive used between the die and leadframe. The component is otherwise considered Pb-Free (RoHS

compatible) as defined above.
Green (RoHS & no Sb/Br): TI defines "Green" to mean Pb-Free (RoHS compatible), and free of Bromine (Br) and Antimony (Sb) based flame retardants (Br or Sb do not exceed 0.1% by weight in homogeneous material)

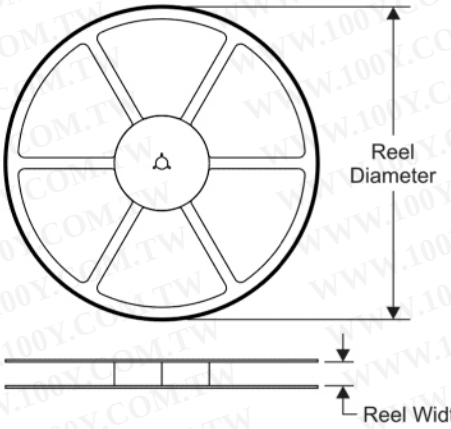
(3) MSL, Peak Temp. -- The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

Important Information and Disclaimer: The information provided on this page represents TI's knowledge and belief as of the date that it is provided. TI bases its knowledge and belief on information provided by third parties, and makes no representation or warranty as to the accuracy of such information. Efforts are underway to better integrate information from third parties. TI has taken and continues to take reasonable steps to provide representative and accurate information but may not have conducted destructive testing or chemical analysis on incoming materials and chemicals. TI and TI suppliers consider certain information to be proprietary, and thus CAS numbers and other limited information may not be available for release.

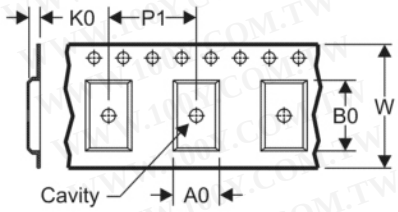
In no event shall TI's liability arising out of such information exceed the total purchase price of the TI part(s) at issue in this document sold by TI to Customer on an annual basis.

TAPE AND REEL INFORMATION

REEL DIMENSIONS

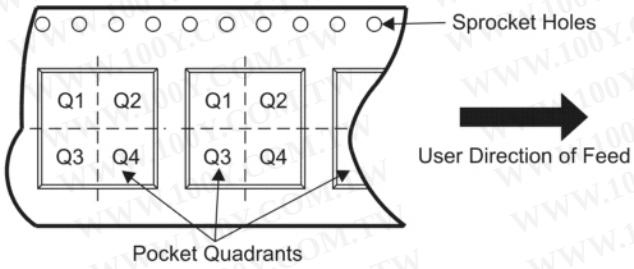


TAPE DIMENSIONS



A0	Dimension designed to accommodate the component width
B0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

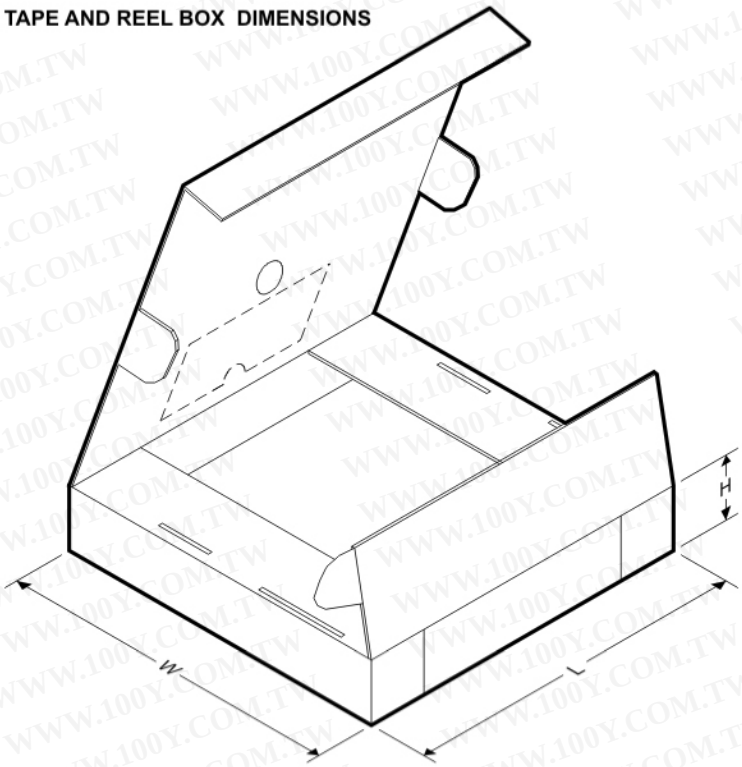
QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
SN74CB3Q3245DBQR	SSOP/ QSOP	DBQ	20	2500	330.0	16.4	6.5	9.0	2.1	8.0	16.0	Q1
SN74CB3Q3245DGVR	TVSOP	DGV	20	2000	330.0	12.4	7.0	5.6	1.6	8.0	12.0	Q1
SN74CB3Q3245GQNR	BGA MICROSTAR JUNIOR	GQN	20	1000	330.0	12.4	3.3	4.3	1.5	8.0	12.0	Q1
SN74CB3Q3245PWR	TSSOP	PW	20	2000	330.0	16.4	6.95	7.1	1.6	8.0	16.0	Q1
SN74CB3Q3245RGYR	VQFN	RGY	20	1000	180.0	12.4	3.8	4.8	1.6	8.0	12.0	Q1
SN74CB3Q3245ZQNR	BGA MICROSTAR JUNIOR	ZQN	20	1000	330.0	12.4	3.3	4.3	1.5	8.0	12.0	Q1
SN74CB3Q3245ZQNR	BGA MICROSTAR JUNIOR	ZQN	20	1000	330.0	12.4	3.3	4.3	1.6	8.0	12.0	Q1

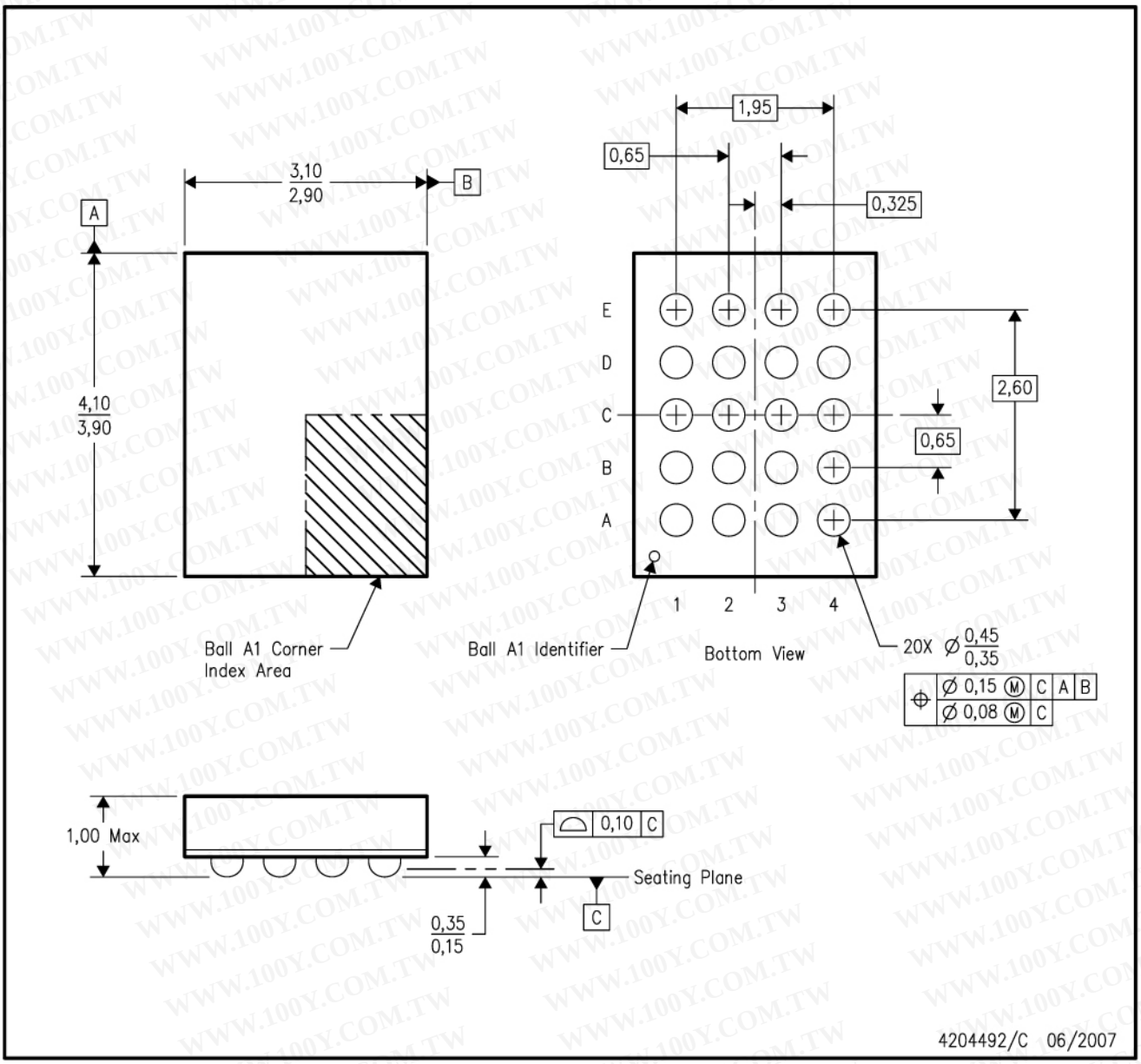
TAPE AND REEL BOX DIMENSIONS



*All dimensions are nominal

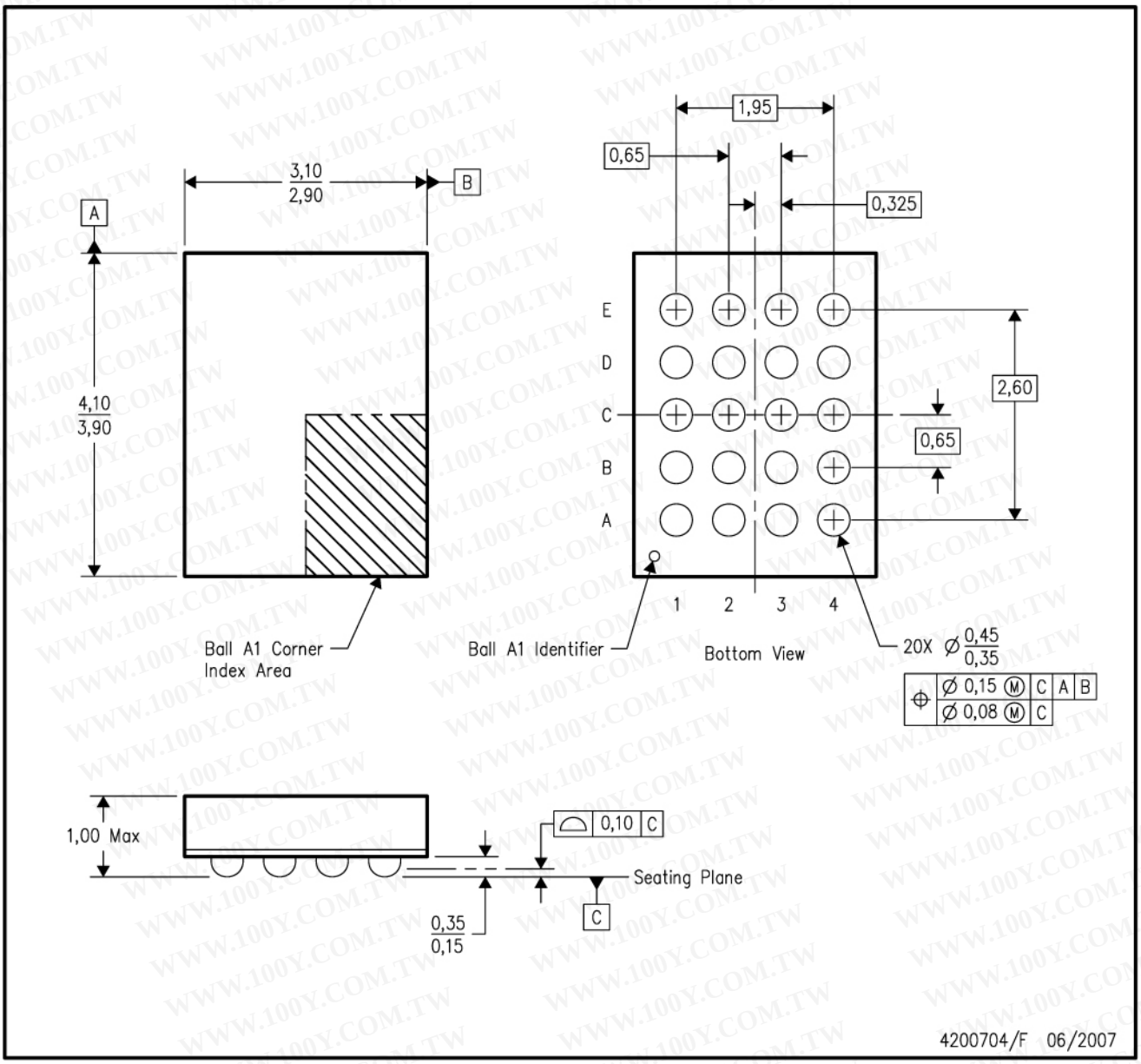
Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
SN74CB3Q3245DBQR	SSOP/QSOP	DBQ	20	2500	346.0	346.0	33.0
SN74CB3Q3245DGVR	TVSOP	DGV	20	2000	346.0	346.0	29.0
SN74CB3Q3245GQNR	BGA MICROSTAR JUNIOR	GQN	20	1000	346.0	346.0	29.0
SN74CB3Q3245PWR	TSSOP	PW	20	2000	346.0	346.0	33.0
SN74CB3Q3245RGYR	VQFN	RGY	20	1000	190.5	212.7	31.8
SN74CB3Q3245ZQNR	BGA MICROSTAR JUNIOR	ZQN	20	1000	346.0	346.0	29.0
SN74CB3Q3245ZQNR	BGA MICROSTAR JUNIOR	ZQN	20	1000	340.5	338.1	20.6

ZQN (R–PBGA–N20) PLASTIC BALL GRID ARRAY



NOTES:
A. All linear dimensions are in millimeters. Dimensioning and tolerancing per ASME Y14.5M–1994.
B. This drawing is subject to change without notice.
C. Falls within JEDEC MO–285 variation BC–2.
D. This package is lead–free. Refer to the 20 GQN package (drawing 4200704) for tin–lead (SnPb).

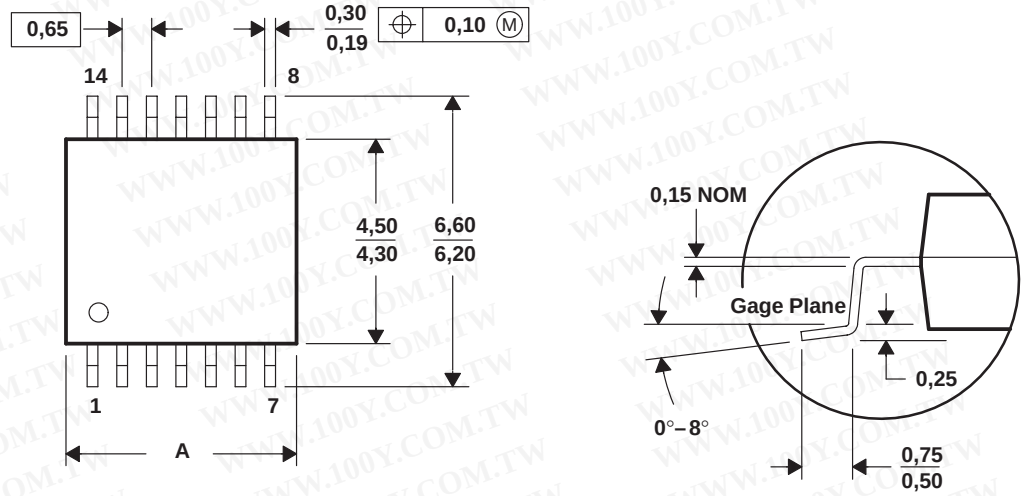
GQN (R–PBGA–N20) PLASTIC BALL GRID ARRAY



NOTES:
A. All linear dimensions are in millimeters. Dimensioning and tolerancing per ASME Y14.5M–1994.
B. This drawing is subject to change without notice.
C. Falls within JEDEC MO–285 variation BC–2.
D. This package is tin–lead (SnPb). Refer to the 20 ZQN package (drawing 4204492) for lead–free.

PW (R-PDSO-G)** **PLASTIC SMALL-OUTLINE PACKAGE**

14 PINS SHOWN

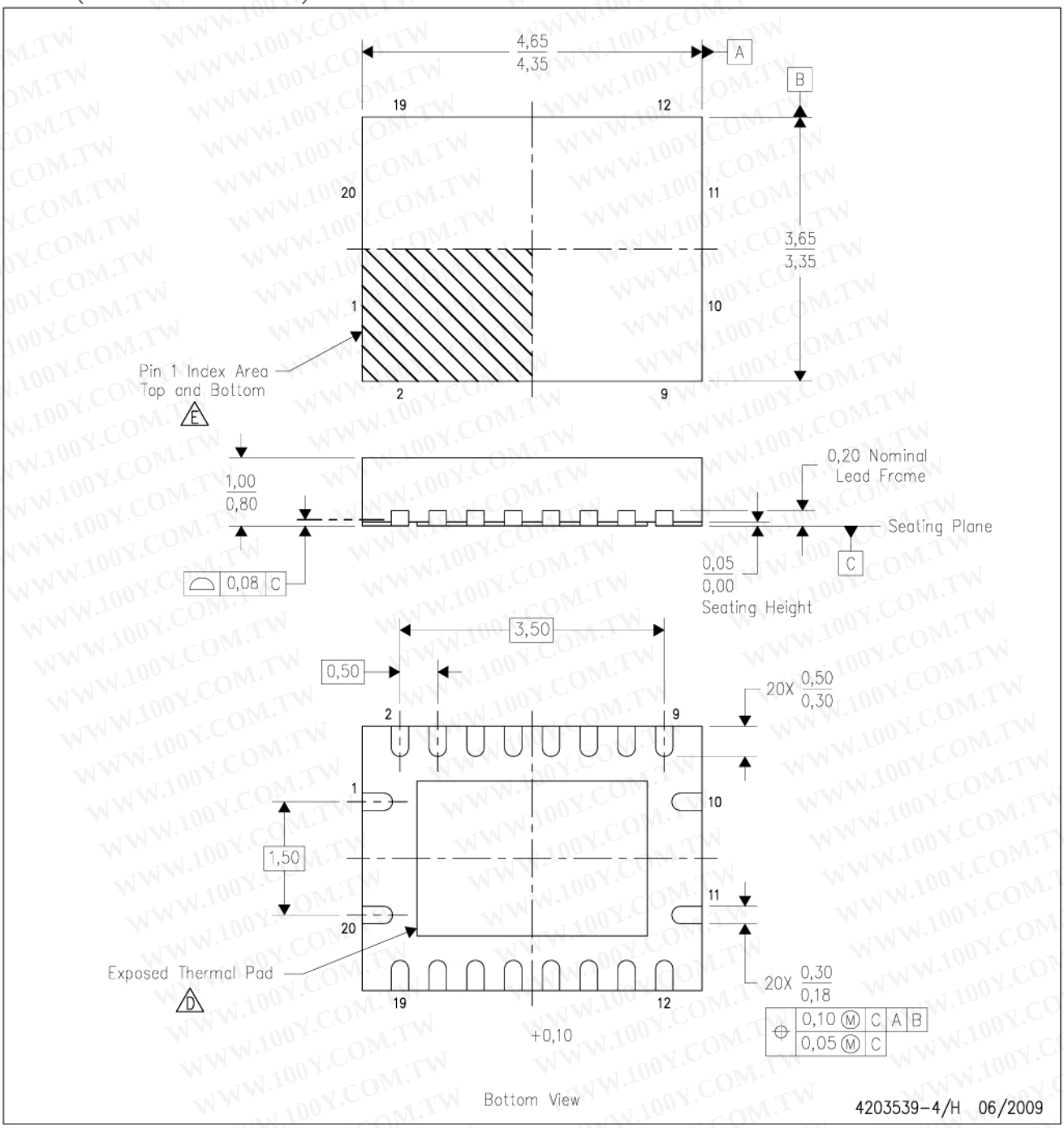


DIM \ PINS **	8	14	16	20	24	28
A MAX	3,10	5,10	5,10	6,60	7,90	9,80
A MIN	2,90	4,90	4,90	6,40	7,70	9,60

4040064/F 01/97

NOTES: A. All linear dimensions are in millimeters.
B. This drawing is subject to change without notice.
C. Body dimensions do not include mold flash or protrusion not to exceed 0,15.
D. Falls within JEDEC MO-153

RGY (R-PVQFN-N20) PLASTIC QUAD FLATPACK NO-LEAD



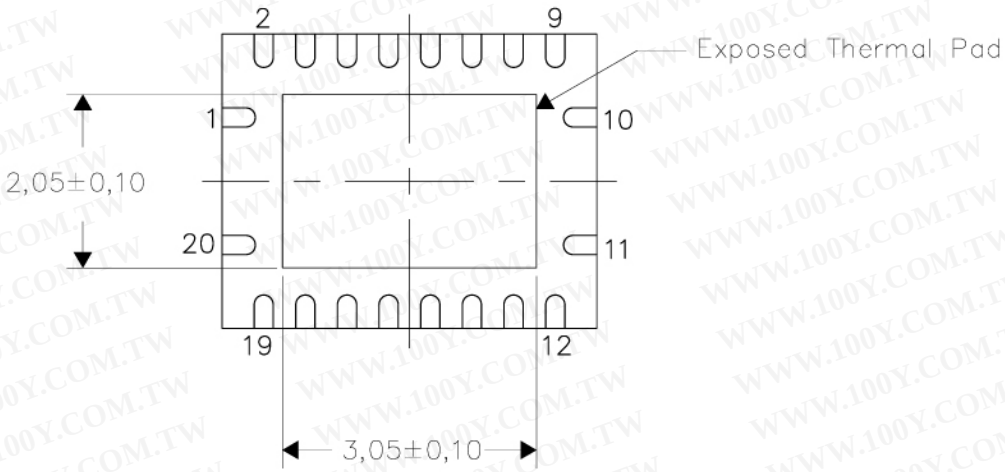
NOTES:
A. All linear dimensions are in millimeters. Dimensioning and tolerancing per ASME Y14.5M-1994.
B. This drawing is subject to change without notice.
C. QFN (Quad Flatpack No-Lead) package configuration.
D. The package thermal pad must be soldered to the board for thermal and mechanical performance. See the Product Data Sheet for details regarding the exposed thermal pad dimensions.
E. Pin 1 identifiers are located on both top and bottom of the package and within the zone indicated. The Pin 1 identifiers are either a molded, marked, or metal feature.
F. Package complies to JEDEC MO-241 variation BC.

THERMAL INFORMATION

This package incorporates an exposed thermal pad that is designed to be attached directly to an external heatsink. The thermal pad must be soldered directly to the printed circuit board (PCB). After soldering, the PCB can be used as a heatsink. In addition, through the use of thermal vias, the thermal pad can be attached directly to the appropriate copper plane shown in the electrical schematic for the device, or alternatively, can be attached to a special heatsink structure designed into the PCB. This design optimizes the heat transfer from the integrated circuit (IC).

For information on the Quad Flatpack No–Lead (QFN) package and its advantages, refer to Application Report, QFN/SON PCB Attachment, Texas Instruments Literature No. SLUA271. This document is available at www.ti.com.

The exposed thermal pad dimensions for this package are shown in the following illustration.

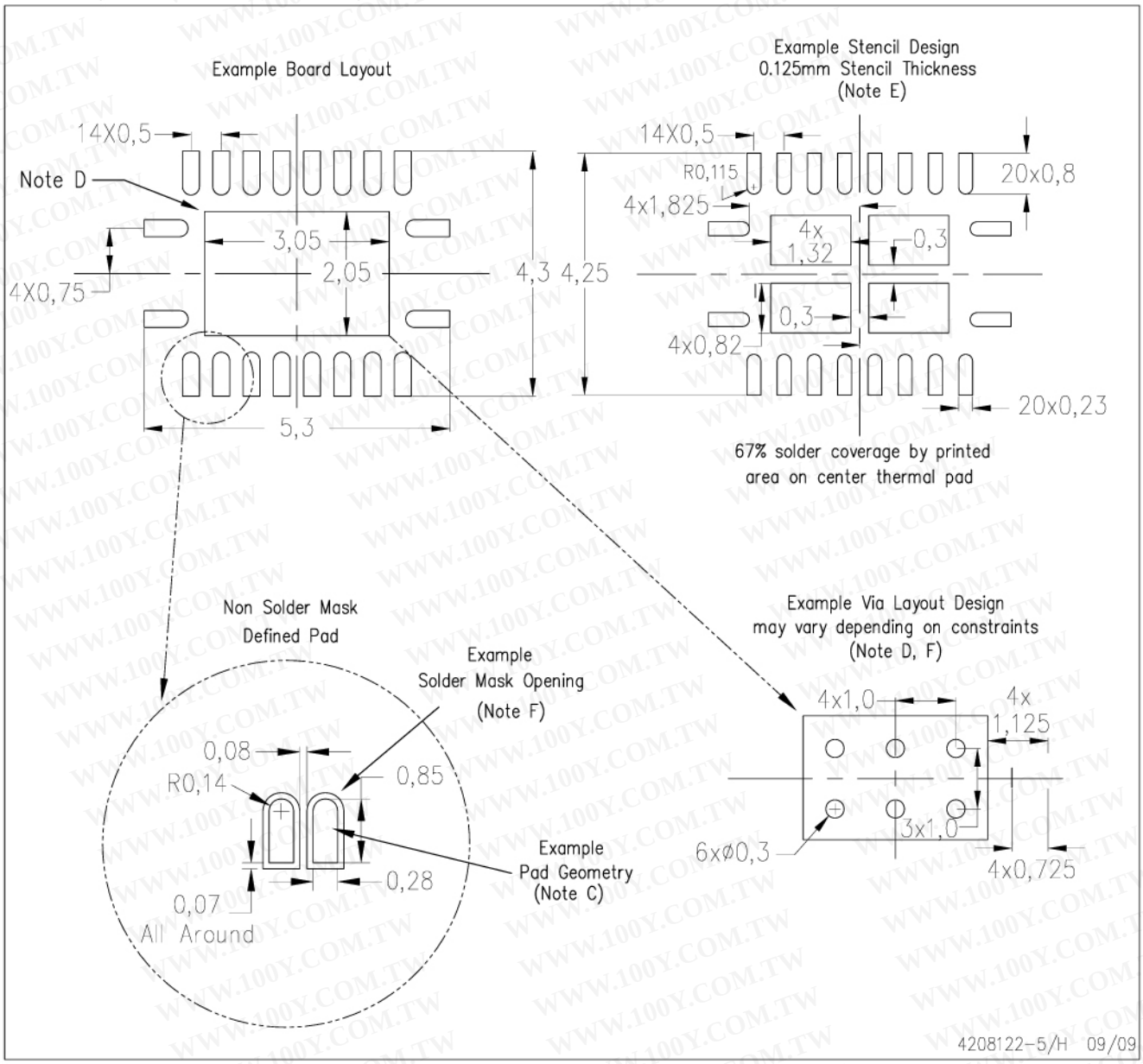


Bottom View

NOTE: All linear dimensions are in millimeters

Exposed Thermal Pad Dimensions

RGY (R-PVQFN-N20)

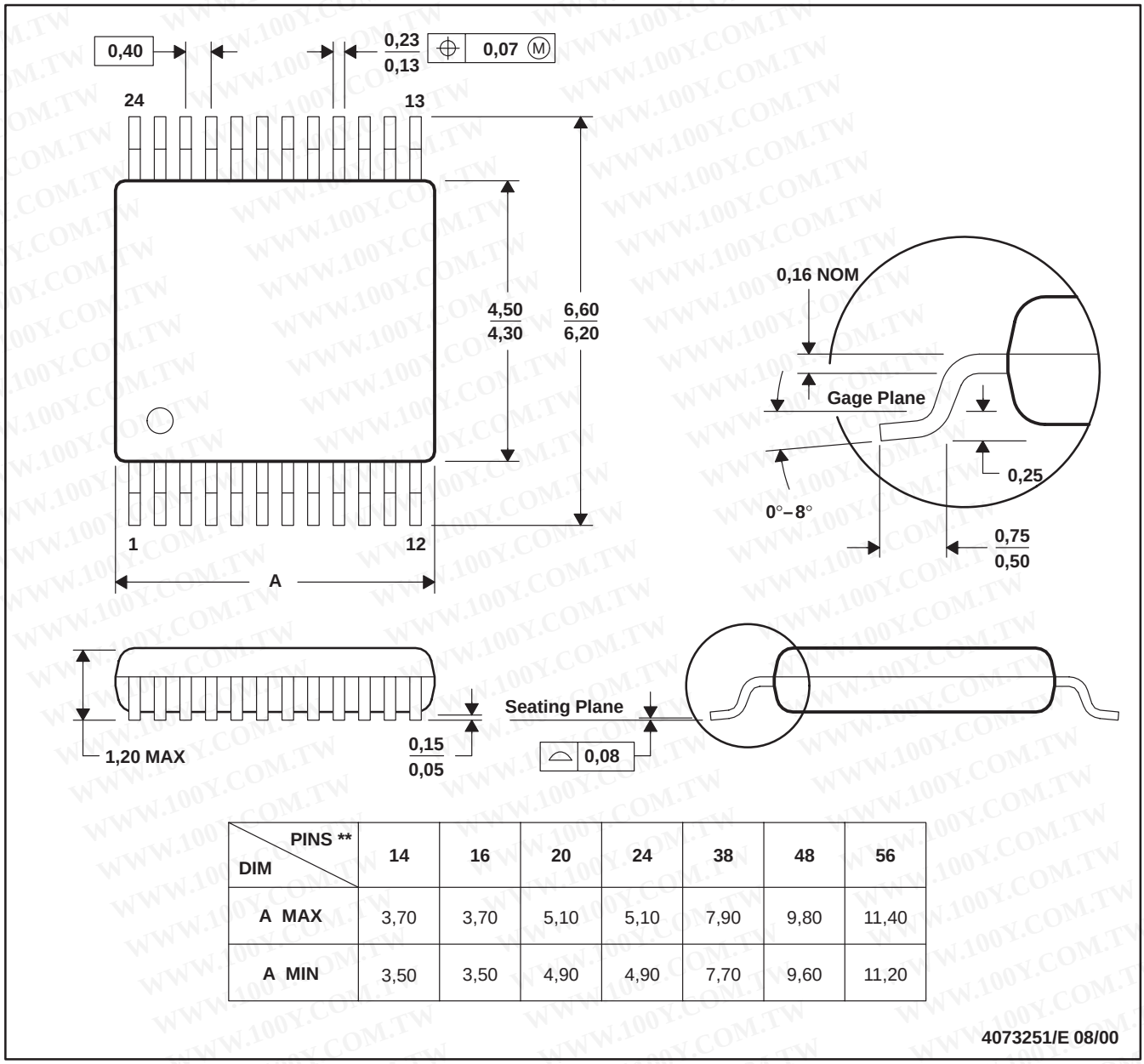


NOTES:
A. All linear dimensions are in millimeters.
B. This drawing is subject to change without notice.
C. Publication IPC-7351 is recommended for alternate designs.
D. This package is designed to be soldered to a thermal pad on the board. Refer to Application Note, Quad Flat-Pack QFN/SON PCB Attachment, Texas Instruments Literature No. SLUA271, and also the Product Data Sheets for specific thermal information, via requirements, and recommended board layout. These documents are available at www.ti.com <http://www.ti.com>.
E. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Refer to IPC 7525 for stencil design considerations.
F. Customers should contact their board fabrication site for minimum solder mask web tolerances between signal pads.

MPDS006C – FEBRUARY 1996 – REVISED AUGUST 2000

DGV (R-PDSO-G)** **PLASTIC SMALL-OUTLINE**

24 PINS SHOWN

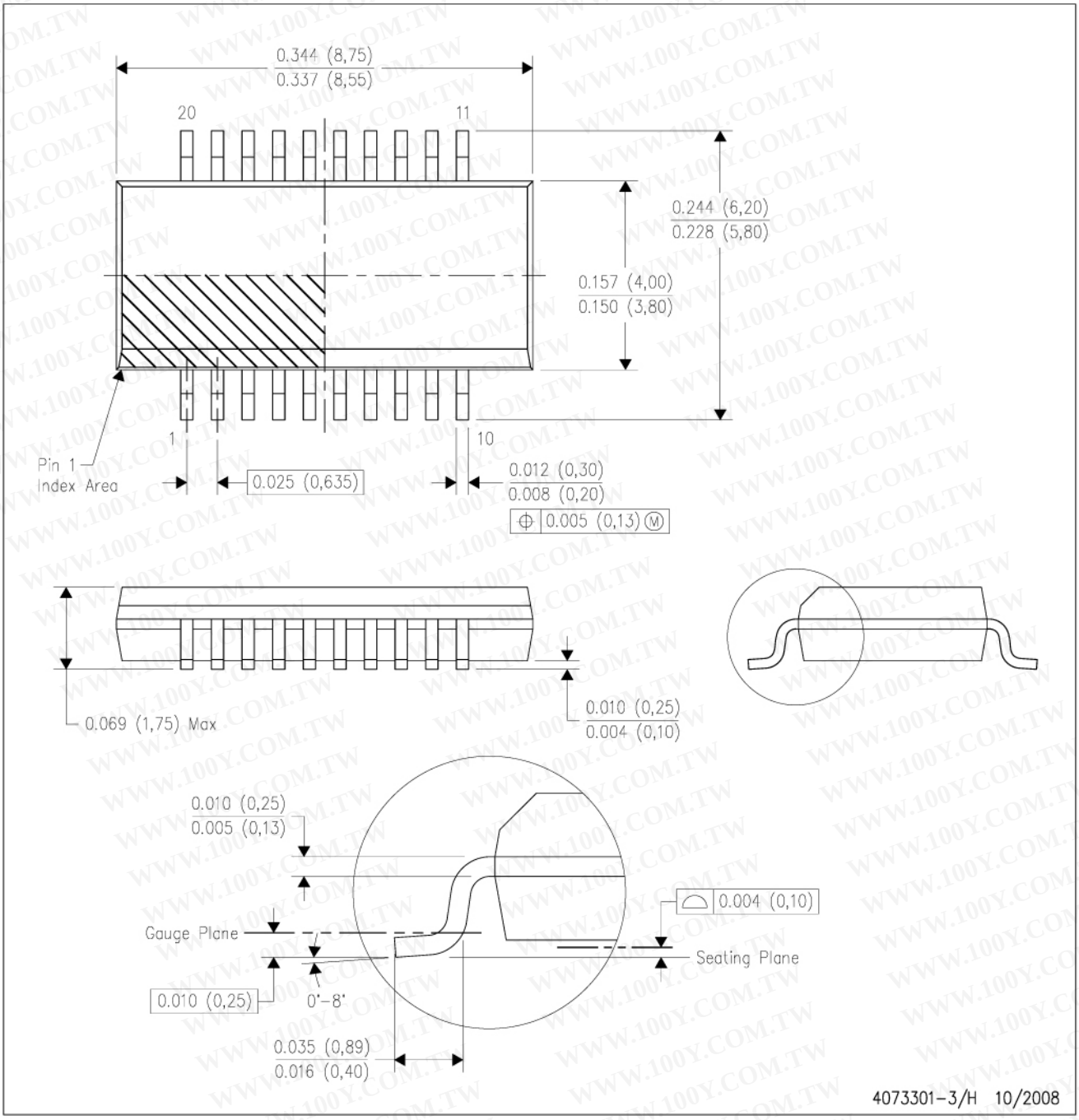


DIM \ PINS **	14	16	20	24	38	48	56
A MAX	3,70	3,70	5,10	5,10	7,90	9,80	11,40
A MIN	3,50	3,50	4,90	4,90	7,70	9,60	11,20

4073251/E 08/00

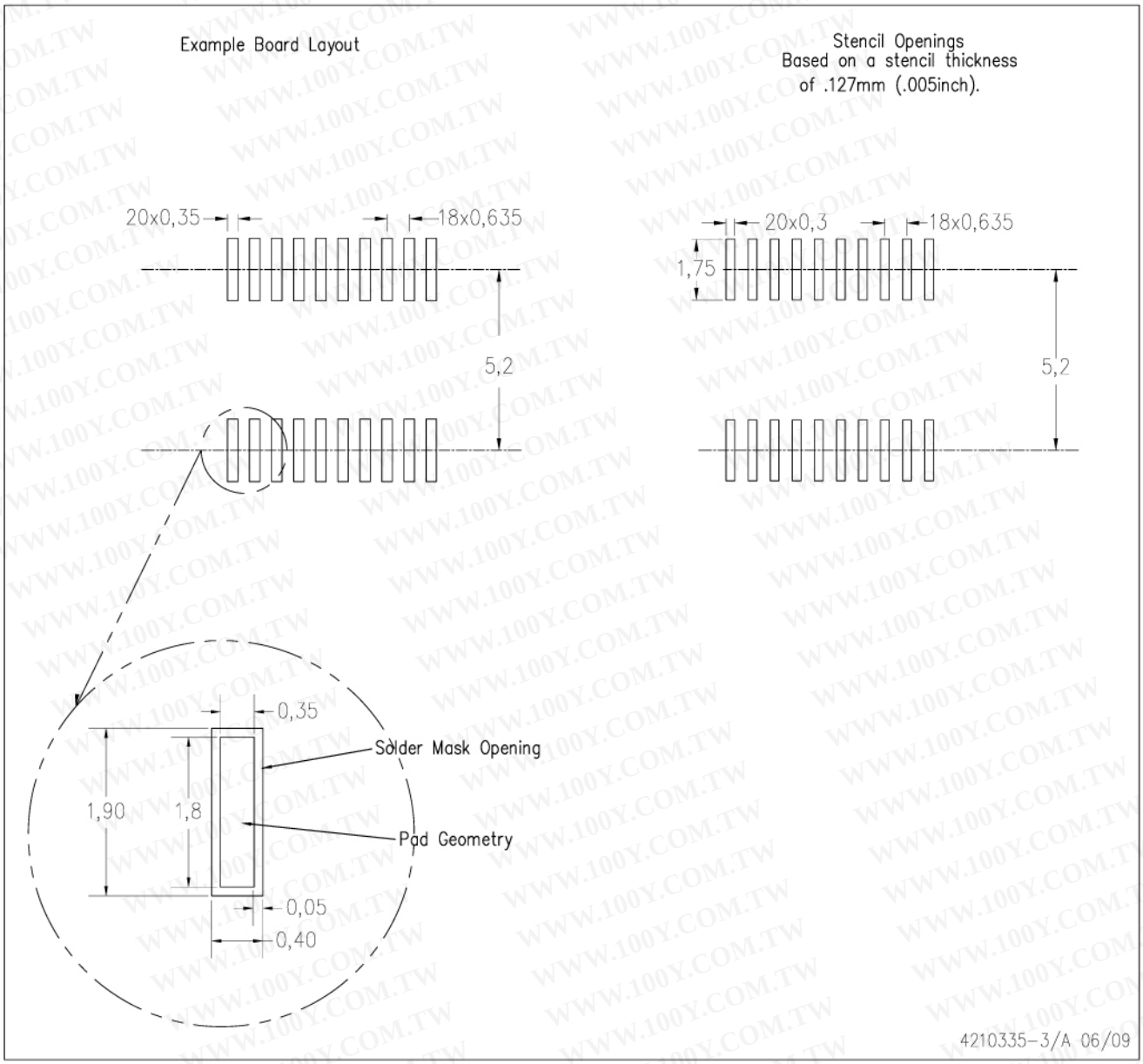
NOTES: A. All linear dimensions are in millimeters.
B. This drawing is subject to change without notice.
C. Body dimensions do not include mold flash or protrusion, not to exceed 0,15 per side.
D. Falls within JEDEC: 24/48 Pins – MO-153
14/16/20/56 Pins – MO-194

DBQ (R-PDSO-G20) PLASTIC SMALL-OUTLINE PACKAGE



NOTES:
A. All linear dimensions are in inches (millimeters).
B. This drawing is subject to change without notice.
C. Body dimensions do not include mold flash or protrusion not to exceed 0.006 (0,15) per side.
D. Falls within JEDEC MO-137 variation AD.

DBQ (R-PDSO-G20)



NOTES:
A. All linear dimensions are in millimeters.
B. This drawing is subject to change without notice.
C. Customers should place a note on the circuit board fabrication drawing not to alter the center solder mask defined pad.
D. Publication IPC-7351 is recommended for alternate designs.
E. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Example stencil design based on a 50% volumetric metal load solder paste. Refer to IPC-7525 for other stencil recommendations.